

2SC2619

Silicon NPN Epitaxial

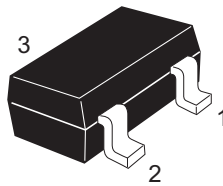
REJ03G0703-0200
 (Previous ADE-208-1070)
 Rev.2.00
 Aug.10.2005

Application

High frequency amplifier

Outline

RENESAS Package code: PLSP0003ZB-A
 (Package name: MPAK)



- 1. Emitter
- 2. Base
- 3. Collector

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	30	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics

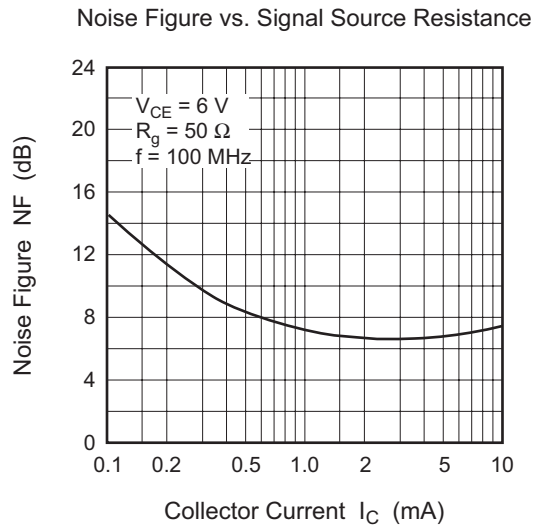
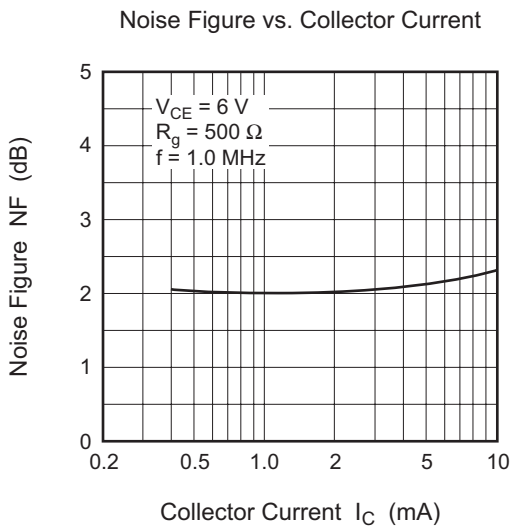
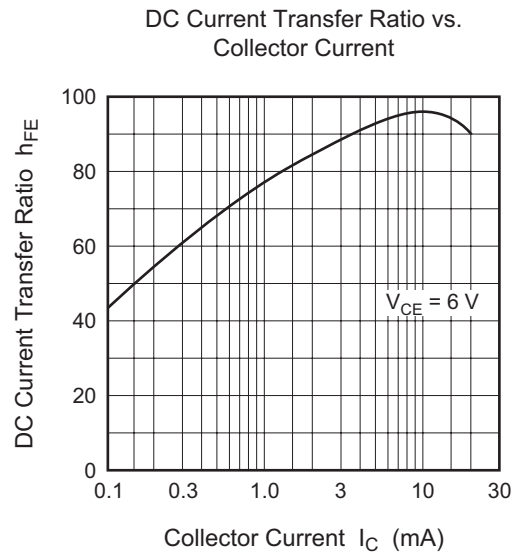
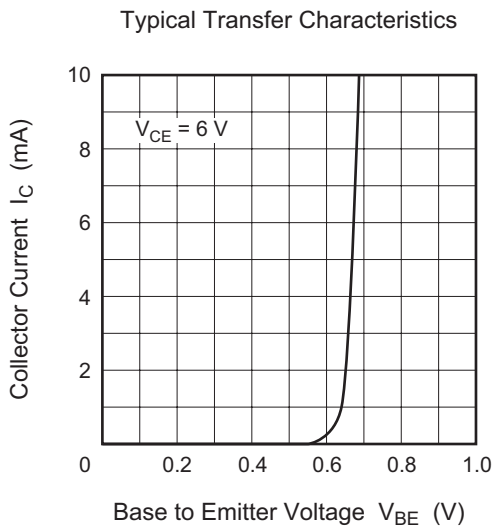
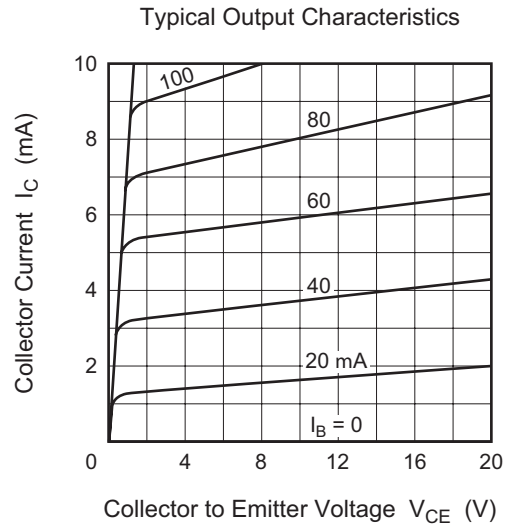
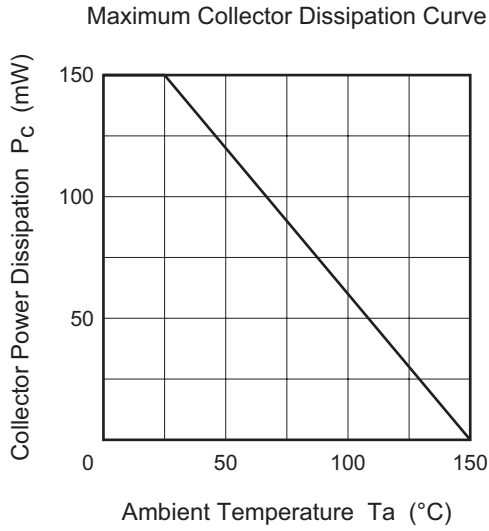
(Ta = 25°C)

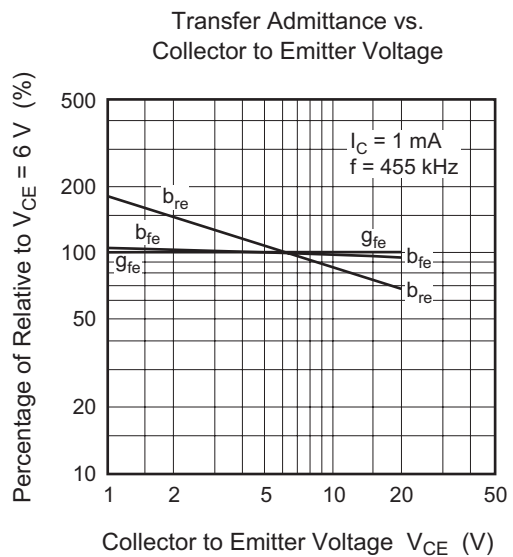
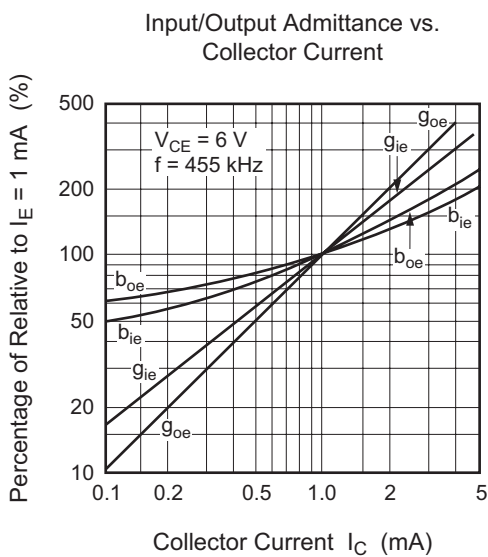
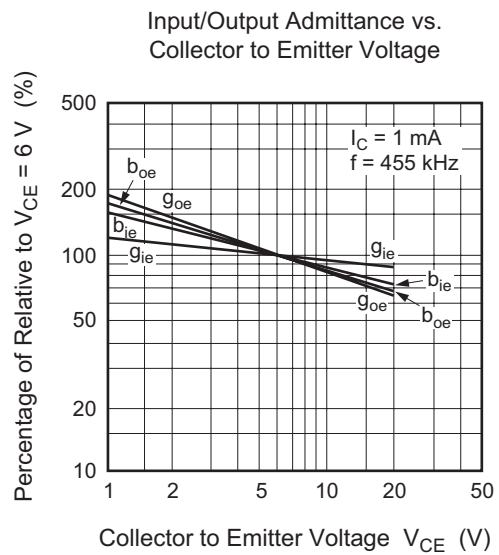
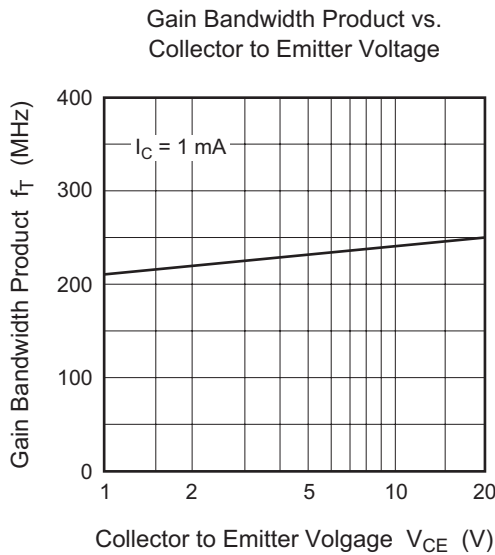
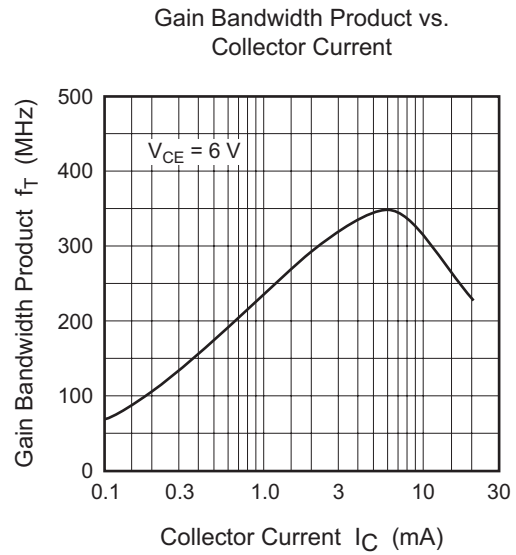
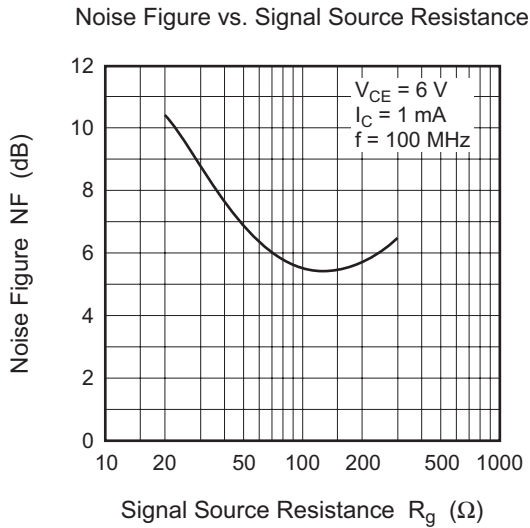
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 20 \text{ V}, I_C = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	60	—	200		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.1	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Gain bandwidth product	f_T	—	230	—	MHz	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector output capacitance	C_{ob}	—	—	3.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Noise figure	NF	—	5.0	—	dB	$V_{CE} = 6 \text{ V}, I_C = 2 \text{ mA}, f = 1 \text{ MHz}, R_g = 500 \Omega$

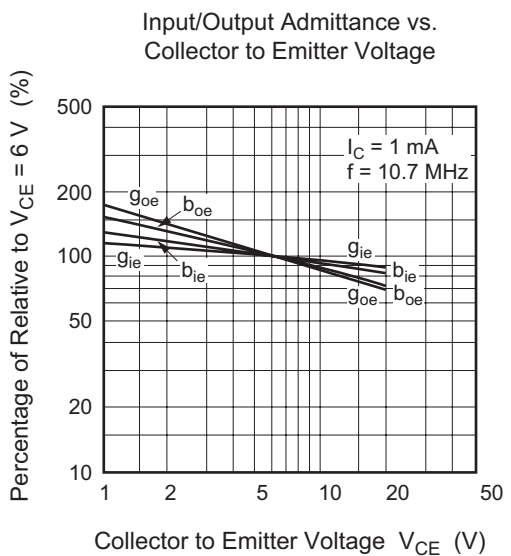
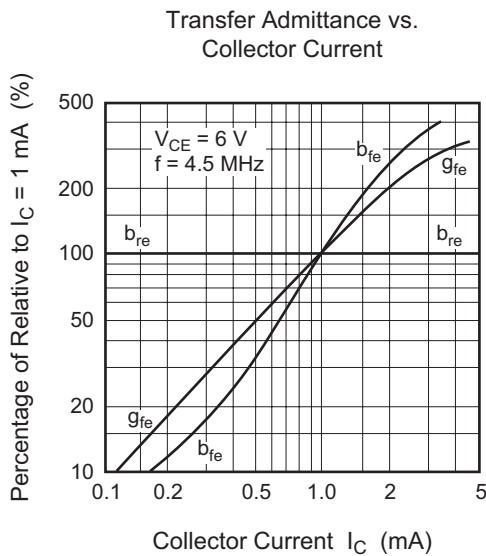
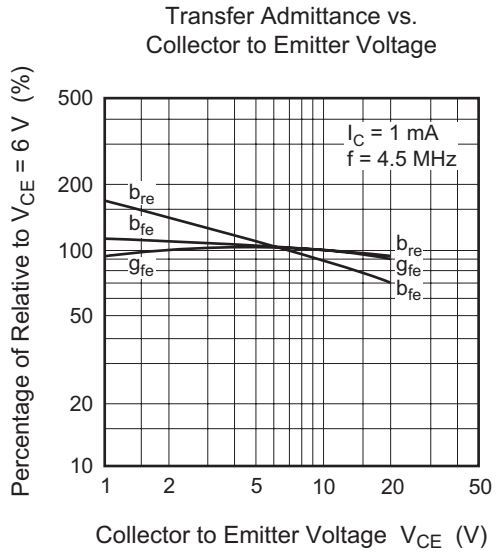
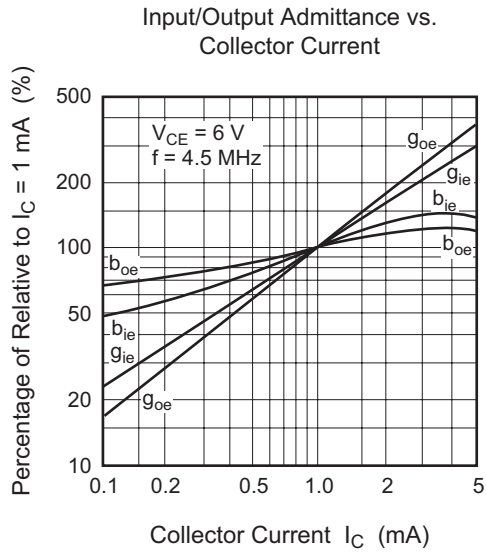
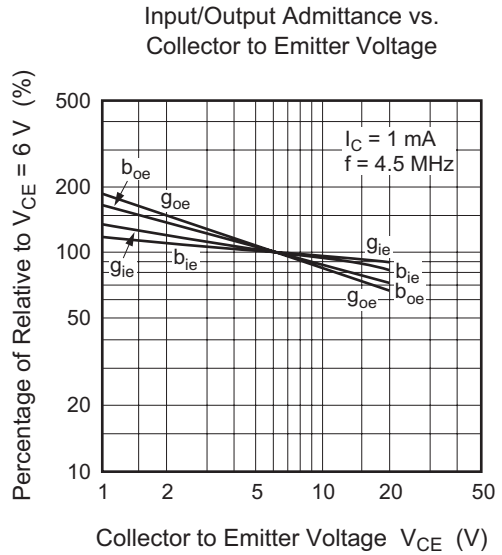
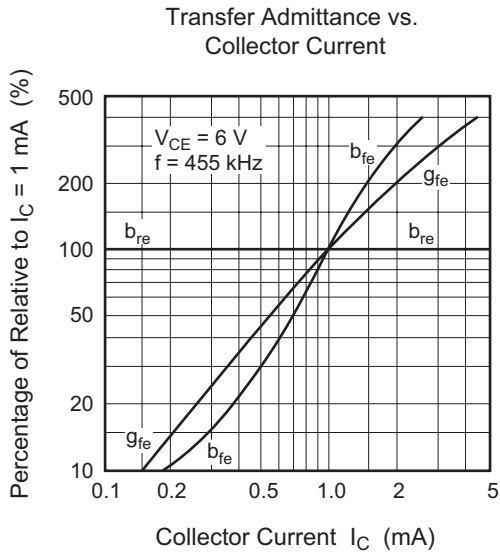
Note: 1. The 2SC2619 is grouped by h_{FE} as follows.

Grade	B	C
Mark	FB	FC
h_{FE}	60 to 120	100 to 200

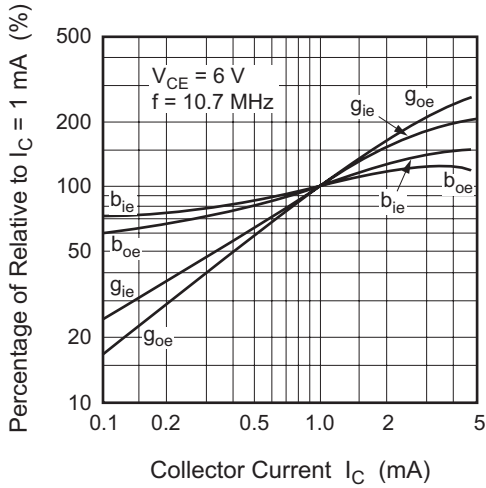
Main Characteristics



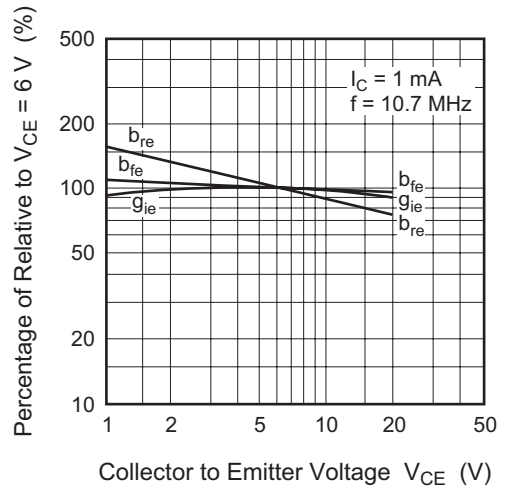




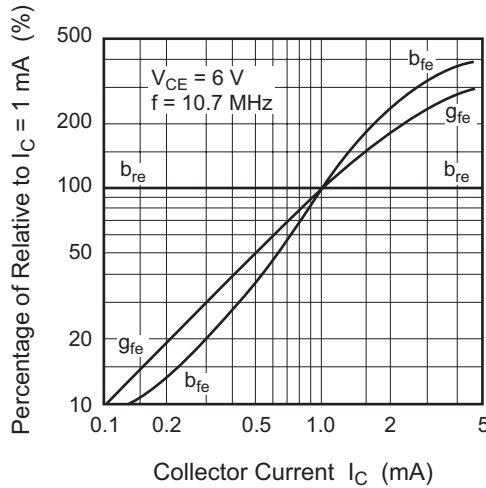
Input/Output Admittance vs. Collector Current



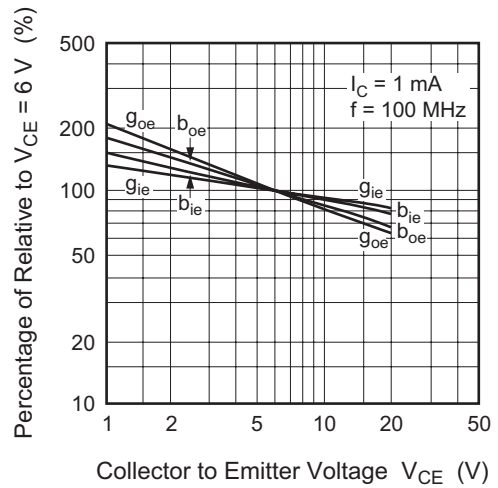
Transfer Admittance vs. Collector to Emitter Voltage



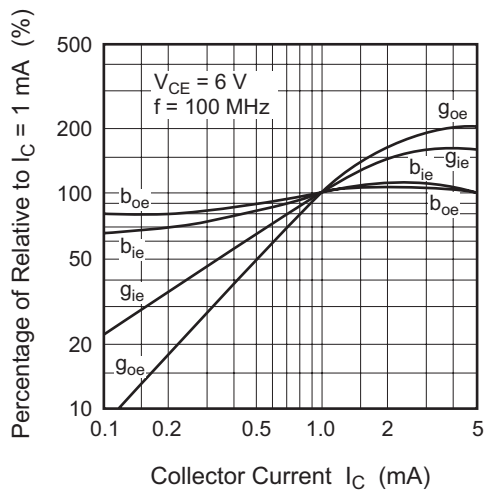
Transfer Admittance vs. Collector Current



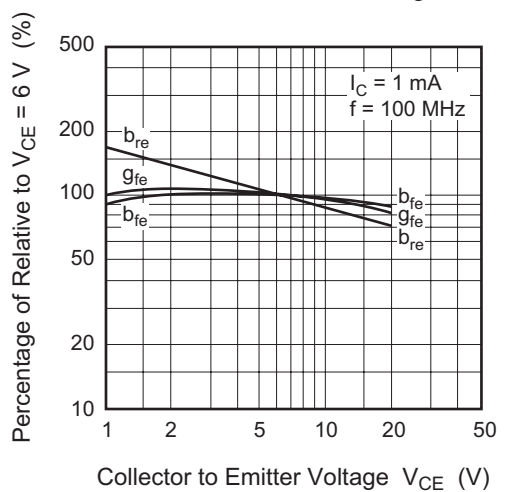
Input/Output Admittance vs. Collector to Emitter Voltage

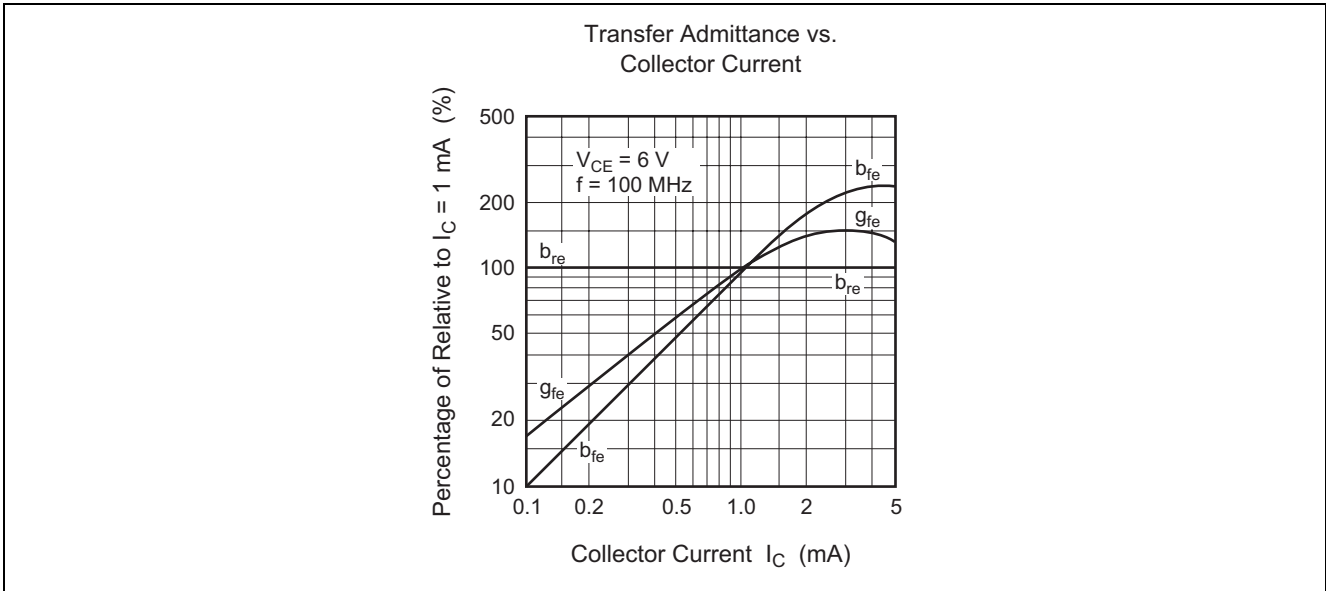


Input/Output Admittance vs. Collector Current

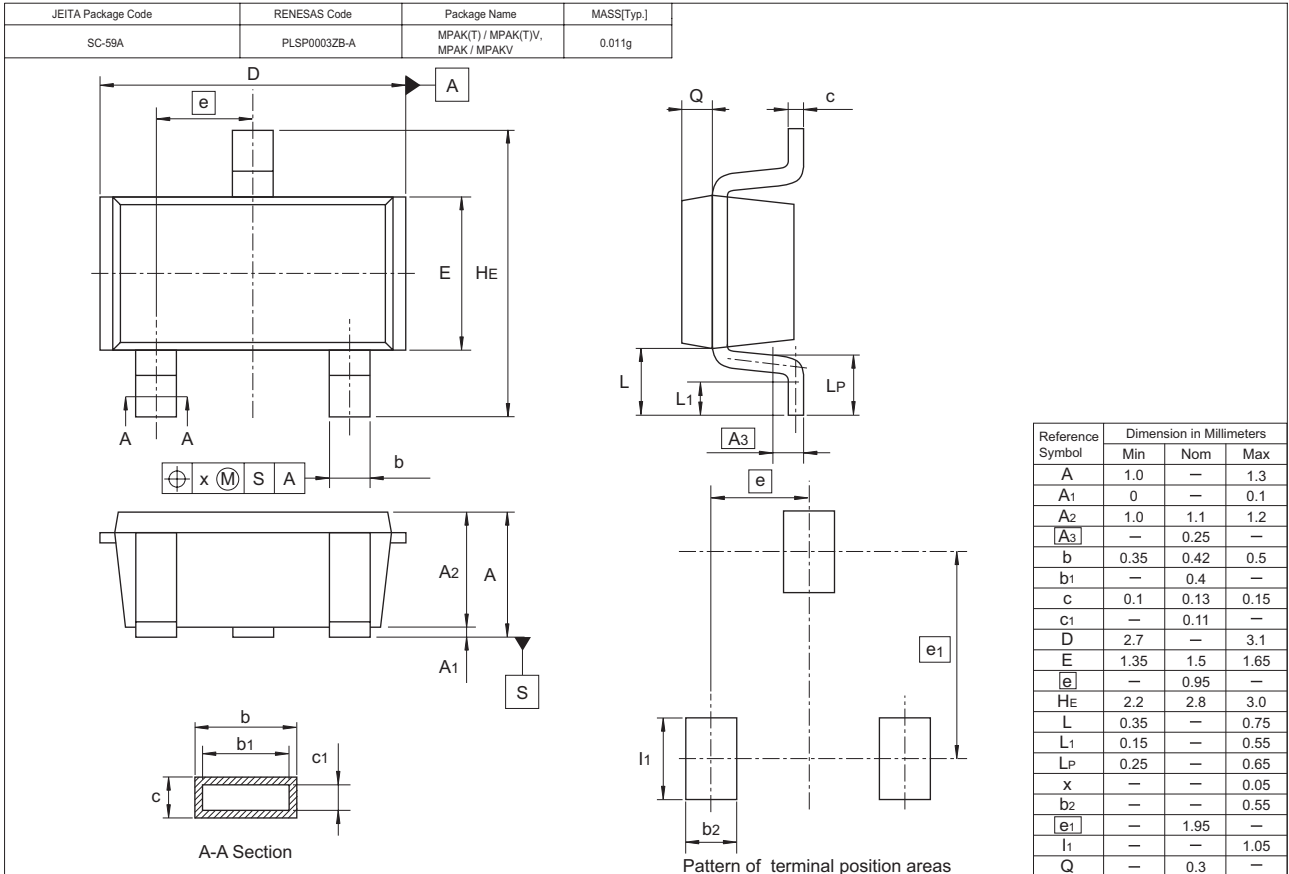


Transfer Admittance vs. Collector to Emitter Voltage





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SC2619FBTR-E	3000	φ 178 mm Reel, 8 mm Emboss Taping
2SC2619FCTR-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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